

Atty. Dkt. No. 035905-0164 (MA-100-I)

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

S. Brad HERNER et al.

Title:

LOW-TEMPERATURE, LOW-

RESISTIVITY HEAVILY

DOPED P-TYPE POLYSILICON

**DEPOSITION** 

Appl. No.:

10/769,047

Filing Date:

1/30/2004

Examiner:

Chen, Bret P.

Art Unit:

1792

Confirmation

7037

Number:

## AMENDMENT AND REPLY UNDER 37 CFR 1.111

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

This communication is rest we to the Non-Final Office Action dated November 1, 2007, concerning the above-referenced patent application.

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this document.

Remarks/Arguments begin on page 5 of this document.

Please amend the application as follows: